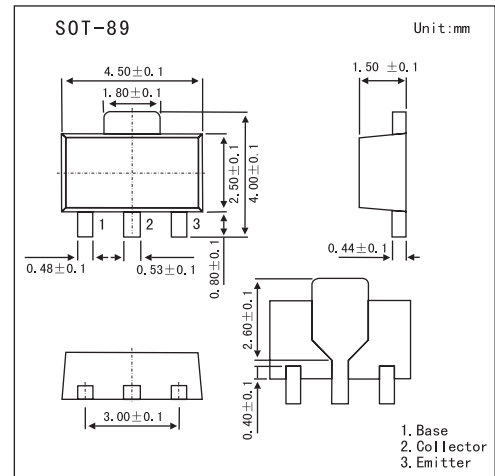


Surface Mount PNP Switching Transistor CXT2907A

■ Features

- High current (max.600mA)
- Low voltage (max.60V)



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	-60	V
Collector-emitter voltage	V _{CE0}	-60	V
Emitter-base voltage	V _{EB0}	-5	V
Collector current (DC)	I _c	-600	mA
Power dissipation	P _D	1.2	W
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-65 to +150	°C
Thermal Resistance	θ _{JA}	104	°C/W

CXT2907A■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base cut-off current	ICBO	IE = 0; VCB = -50 V			-10	nA
		IE = 0; VCB = -50 V; Tj = 125 °C			-10	μ A
Emitter-base cut-off current	IEBO	IC = 0; VEB = -5 V			-50	nA
DC current gain	hFE	IC = -0.1 mA; VCE = -10 V	75			
		IC = -1 mA; VCE = -10 V	100			
		IC = -10 mA; VCE = -10 V	100			
		IC = -150 mA; VCE = -10 V	100		300	
		IC = -500 mA; VCE = -10 V	50			
Collector-emitter saturation voltage	VCEsat	IC = -150 mA; IB = -15mA			-0.4	V
		IC = -500 mA; IB = -50 mA			-1.6	V
Base-emitter saturation voltage	VBEsat	IC = -150 mA; IB = -15 mA			-1.3	V
		IC = -500 mA; IB = -50 mA			-2.6	V
Turn-on time	ton	VCC=30V, VBE=-0.5V, IC=-150mA, IB1=-15mA			45	ns
Delay time	td				10	ns
Rise time	tr				40	ns
Turn-off time	toff	VCC=-6.0V, IC=-150mA, IB1=IB2=-15mA			100	ns
Storage time	ts				80	ns
Fall time	tf				30	ns
Transition frequency	fr	IC = -50 mA; VCE = -20 V; f = 100 MHz	200			MHz

CXT2907A

Typical Characteristics

